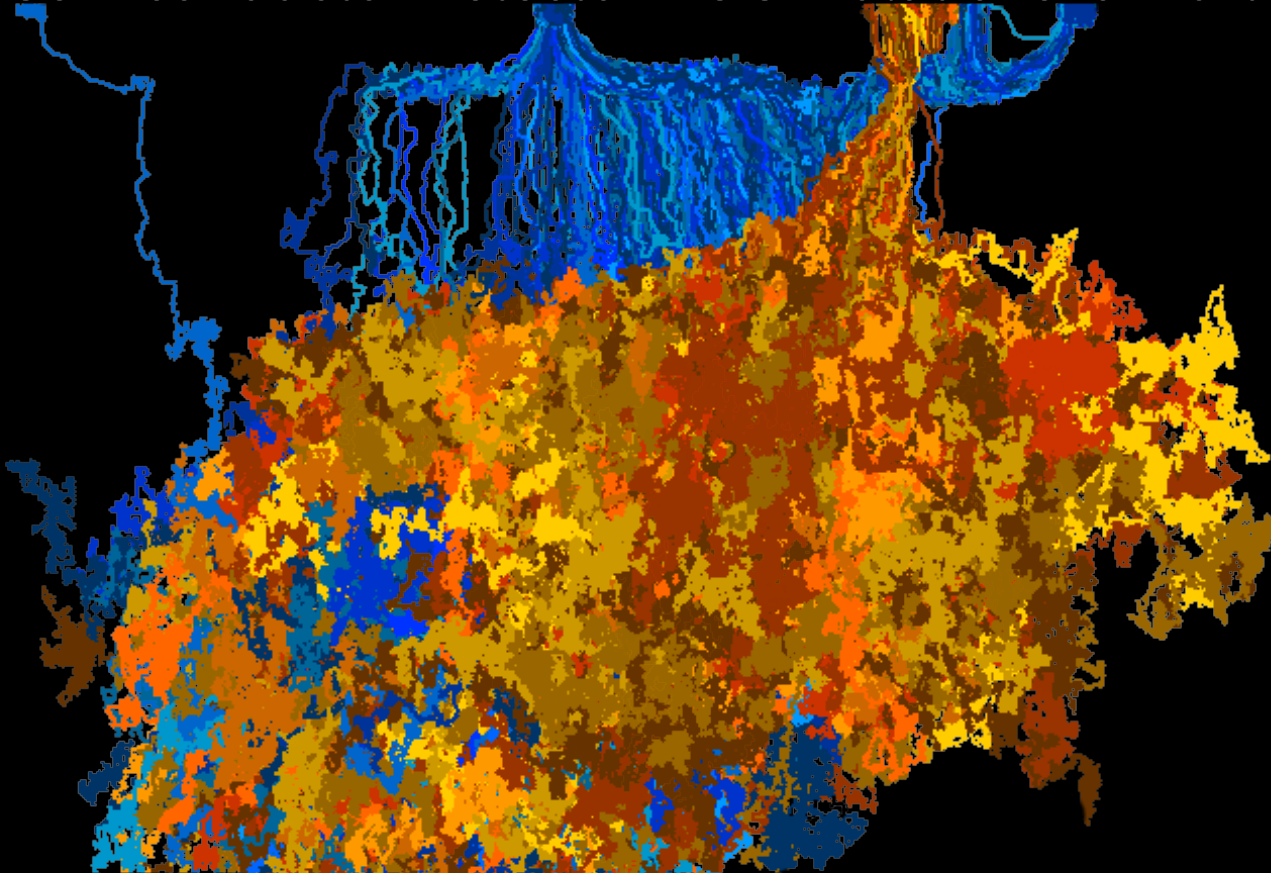




[cern.ch/allpix-squared](https://cern.ch/allpix-squared)

# Allpix Squared

Semiconductor Detector MC Simulations for Particle Physics and Beyond



Paul Schütze, DESY

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1<sup>st</sup> DRD3 Week, CERN

20 June 2024

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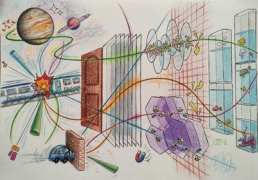
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# Semiconductor Detector MC Simulations DRD3

Community Meeting 22-23/03/2023  
Implementation of TF3  
Solid State Detectors

- Complexity of detectors increases, more and more technologies available, different approaches combined (e.g. monolithic + LGAD)
  - Necessity of MC simulations growing
  - Some sensors / setups impractical to simulate in TCAD (time limitation, stochastics)
  - Community needs *common* flexible, tested & supported MC simulation tools
- Using Monte Carlo methods to describe detector response is not new
- Creation & proliferation of many different codes for detector simulation
  - Experiment-specific
  - Specialized on specific detectors
  - Inclusion only of effects relevant to that one simulation
  - Written as part of a PhD thesis, abandoned afterwards
- Would be great to collate features in commonly maintained software (->SM)
  - Having several tools is valuable as testbed for algorithms
  - Well-maintained & supported common software will significantly ease use in community

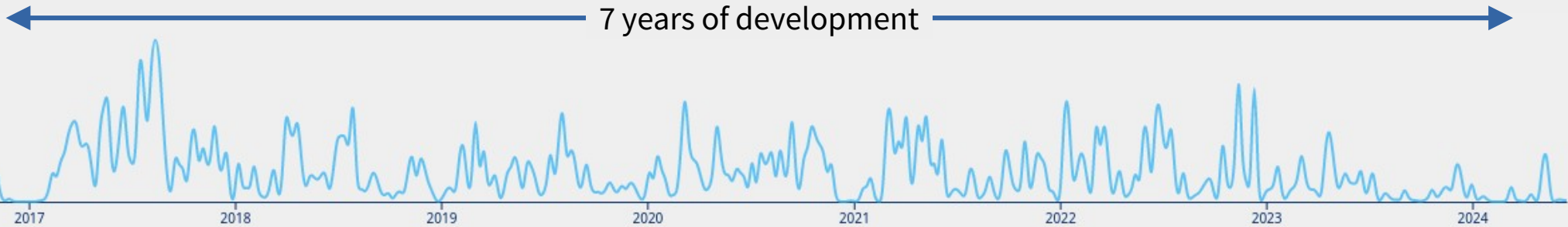
# The Allpix<sup>2</sup> Framework



- Development of framework started within **CLICdp Collaboration**
- Now > 7 years of development with
  - 51 releases, current version 3.1.0
  - 5 user workshops
  - Close to 70 code contributors

Development based on four principles:

- I. Integration of Existing Toolkits
- II. Well-Tested & Validated Algorithms
- III. Low Entry Barrier for New Users
- IV. Clean & Maintainable Code



8882 commits | Last commit ≈ 4 days ago



# I. Integration of Existing Toolkits

Many very powerful tools developed and employed over decades of detector R&D  
Leverage their capabilities by providing interfaces for their integration

**Geant4** – simulating interactions of particles passing through matter

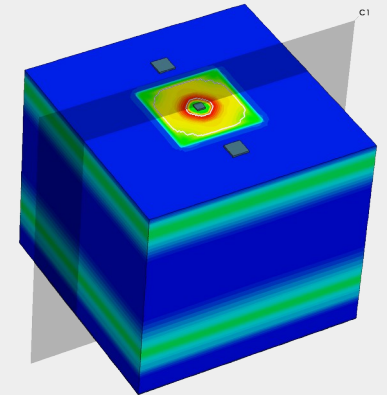
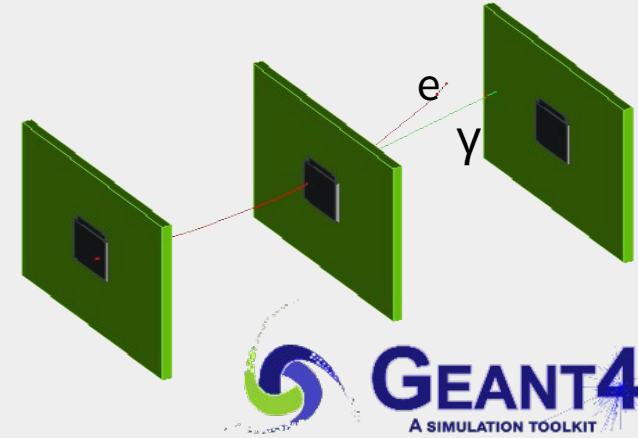
- Detailed simulation of many interactions & processes
- Provide abstraction layer to auto-generate models and run simulation

**TCAD** – detailed simulation of field configuration, sensor behavior

- Tools & knowledge widely spread in community
- Provide possibility to import results to complement MC simulations

**CRY** – Cosmic-ray shower generator

**HepMC3** – Reading HepMC event records from Event Generators





# II. Well-Tested & Validated Algorithms

Simulations provide insights into physical processes – but only if they model them correctly!

- Validation of algorithms is a crucial and time-consuming process
- So far **5 User workshops** for exchange of the community, discussions, planning...

- Validating as much as possible against data
- Publishing reference studies including full simulation configuration used
- Providing automated tests for every new feature

Nuclear Inst. and Methods in Physics Research, v.1 (2018) 164-172

Content lists available on ScienceDirect  
Nuclear Inst. and Methods in Physics Research, A

AlpSi<sup>2</sup>: a modular simulation framework for silicon detectors

S. Spangnagl<sup>1</sup>, A. Wahlen<sup>1</sup>, D. Hryda<sup>1</sup>, N. Allpauer Teufel<sup>1</sup>, M. Brossi<sup>1</sup>, D. Dambach<sup>1</sup>, S. Gamm<sup>1</sup>, A. Nöcker<sup>1</sup>, P. Schmitt<sup>1</sup>, M. Verste<sup>1</sup>

1 DESY, Hamburg, Germany

ARTICLE INFO  
ABSTRACT  
KEYWORDS

1. Introduction  
Detailed simulations of segmented silicon detectors are a crucial tool for the development and validation of reconstruction algorithms. In this paper we describe the development and validation of AlpSi<sup>2</sup>, a modular simulation framework for silicon detectors. AlpSi<sup>2</sup> is designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations. AlpSi<sup>2</sup> is a modular simulation framework for silicon detectors, designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations.

2. Framework architecture  
AlpSi<sup>2</sup> is built as a modular framework which separates simulation components from the event generation simulation. The framework is designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations.

3. Conclusions  
AlpSi<sup>2</sup> is a modular simulation framework for silicon detectors, designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations.

Nuclear Inst. and Methods in Physics Research, v.1 (2018) 164-172

Content lists available on ScienceDirect  
Nuclear Inst. and Methods in Physics Research, A

Combining TCAD and Monte Carlo methods to simulate CMOS pixel sensors with a small collection of events using the AlpSi<sup>2</sup> framework

D. Dambach, K. Dost, D. Hryda, M. Musker, A. Nöcker, W. Soosey, S. Spangnagl

1 DESY, Hamburg, Germany

ARTICLE INFO  
ABSTRACT  
KEYWORDS

1. Introduction  
Integrated Silicon CMOS technologies with sub-100 nm feature sizes are becoming increasingly important for the development of silicon detectors. In this paper we describe the development and validation of AlpSi<sup>2</sup>, a modular simulation framework for silicon detectors. AlpSi<sup>2</sup> is designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations.

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Nuclear Inst. and Methods in Physics Research, v.1 (2018) 164-172

Content lists available on ScienceDirect  
Nuclear Inst. and Methods in Physics Research, A

Transient Monte Carlo simulations for the optimisation and characterisation of monolithic silicon sensors

R. Balogh<sup>1</sup>, A. Brach<sup>1</sup>, E. Bruchmann<sup>1</sup>, M. Cuyepohl<sup>1</sup>, D. Dambach<sup>1</sup>, K. Dost<sup>1</sup>, L. Hub<sup>1</sup>, A. Krennert<sup>1</sup>, A. Krüger<sup>1</sup>, L. Linsen<sup>1</sup>, M. Musker<sup>1</sup>, P. Schmitt<sup>1</sup>, W. Soosey<sup>1</sup>, S. Spangnagl<sup>1</sup>, T. Vana<sup>1</sup>

1 DESY, Hamburg, Germany

ARTICLE INFO  
ABSTRACT  
KEYWORDS

1. Introduction  
The simulation of silicon detectors is a complex task, involving the simulation of the detector structure, the simulation of the detector operation, and the simulation of the detector response. In this paper we describe the development and validation of AlpSi<sup>2</sup>, a modular simulation framework for silicon detectors. AlpSi<sup>2</sup> is designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations.

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Jinst

Proceedings of the 17th International Conference on Silicon Detectors

AlpSi<sup>2</sup> – silicon detector Monte Carlo simulations for particle physics and beyond

S. Spangnagl<sup>1</sup> and P. Schmitt<sup>1</sup>

1 DESY, Hamburg, Germany

ARTICLE INFO  
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AlpSi<sup>2</sup>: Recent Developments and Applications

S. Spangnagl<sup>1</sup>, T. Brossi<sup>1</sup>, K. Dost<sup>1</sup>, M. Musker<sup>1</sup>, M. Verste<sup>1</sup>, P. Schmitt<sup>1</sup>, W. Soosey<sup>1</sup>, S. Gamm<sup>1</sup>, A. Nöcker<sup>1</sup>, P. Schmitt<sup>1</sup>, M. Verste<sup>1</sup>

1 DESY, Hamburg, Germany

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Simulating Monolithic Active Pixel Sensors: A Technology-Independent Approach Using Generic Profiles

R. Balogh<sup>1</sup>, D. Dambach<sup>1</sup>, D. Hryda<sup>1</sup>, M. Musker<sup>1</sup>, W. Soosey<sup>1</sup>, S. Spangnagl<sup>1</sup>, T. Vana<sup>1</sup>

1 DESY, Hamburg, Germany

ARTICLE INFO  
ABSTRACT  
KEYWORDS

1. Introduction  
The simulation of monolithic active pixel sensors (MAPS) is a complex task, involving the simulation of the detector structure, the simulation of the detector operation, and the simulation of the detector response. In this paper we describe the development and validation of AlpSi<sup>2</sup>, a modular simulation framework for silicon detectors. AlpSi<sup>2</sup> is designed to be used for the simulation of silicon detectors in a wide range of applications, from the development of reconstruction algorithms to the validation of Monte Carlo simulations.

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NIMA 901 (2018) 164 – 172  
doi:10.1016/j.nima.2018.06.020

NIMA 964 (2020) 163784  
doi:10.1016/j.nima.2020.163784

NIMA 1031 (2022) 166491  
doi:10.1016/j.nima.2022.166491

JINST 17 (2022) C09024  
doi:10.1088/1748-0221/17/09/C09024

In preparation...

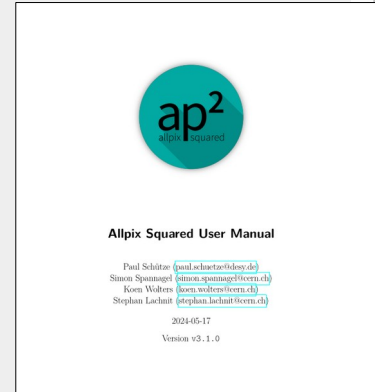
In preparation...



# III. Low Entry Barrier for New Users

Simulation frameworks often very complex:  
code complexity, lack of documentation, physics

- Allpix Squared facilitates quick starts:
  - Extensive documentation / [user manual](#)
  - [Public forum](#) for help & exchange
  - Human-readable configuration files
  - Support for physical units
  - No coding or code-reading required
- Successfully used e.g. in university education, summer schools, ...

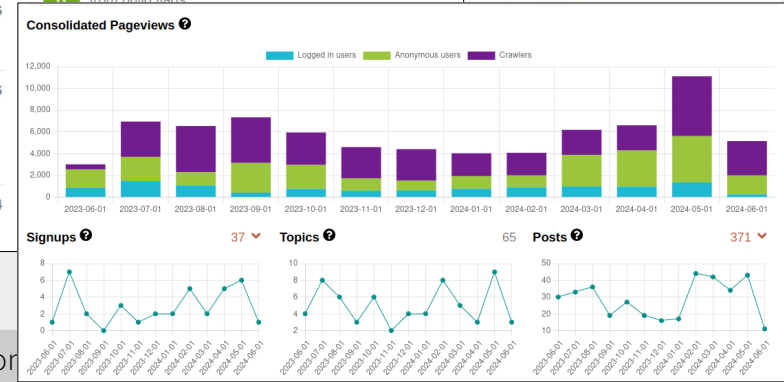


```
1 [AllPix]
2 log_level = "INFO"
3 number_of_events = 500000
4 detectors_file = "telescope.conf"
```

```
[GeometryBuilderGeant4]
world_material = "air"
```

```
[DepositionGeant4]
physics_list = FTFP_BERT_LIV
particle_type = "Pi+"
number_of_particles = 1
beam_energy = 120GeV
# ...
```

```
[ElectricFieldReader]
```





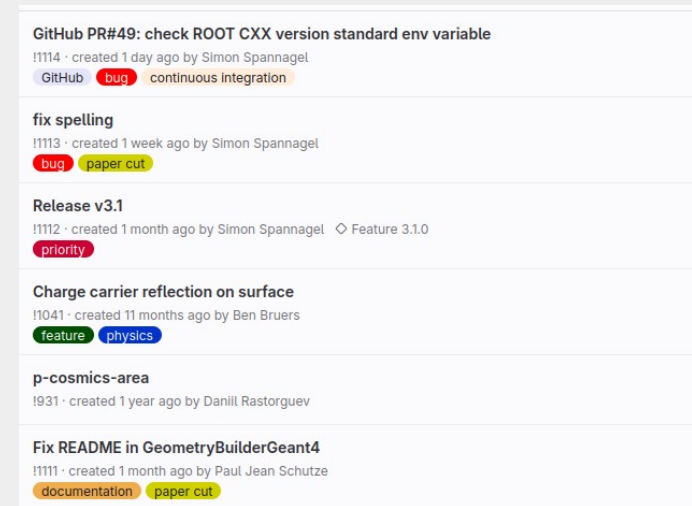
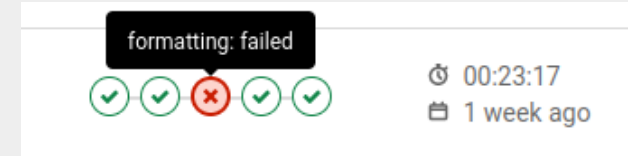
# IV. Clean & Maintainable Code

Collaborative software development requires well-defined procedures –  
 Otherwise quickly becomes unmaintainable

Allpix Squared implements *best practices* for software development

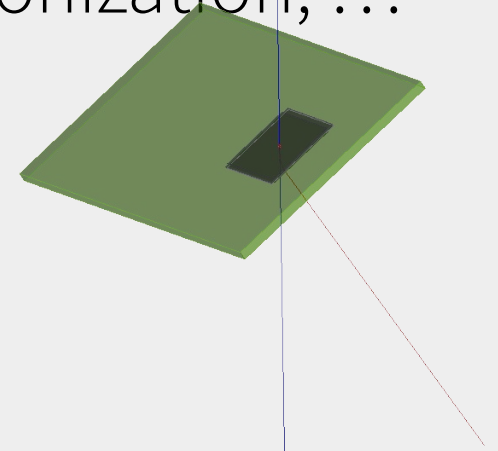
- Permissive MIT open-source license
- Semantic versioning (major.feature.patch)
- Extensive code reviews via merge requests
- Strict enforcement of coding conventions & formatting
- Regular static code analysis
- Following C++17 Standards

... see later for contribution cookbook



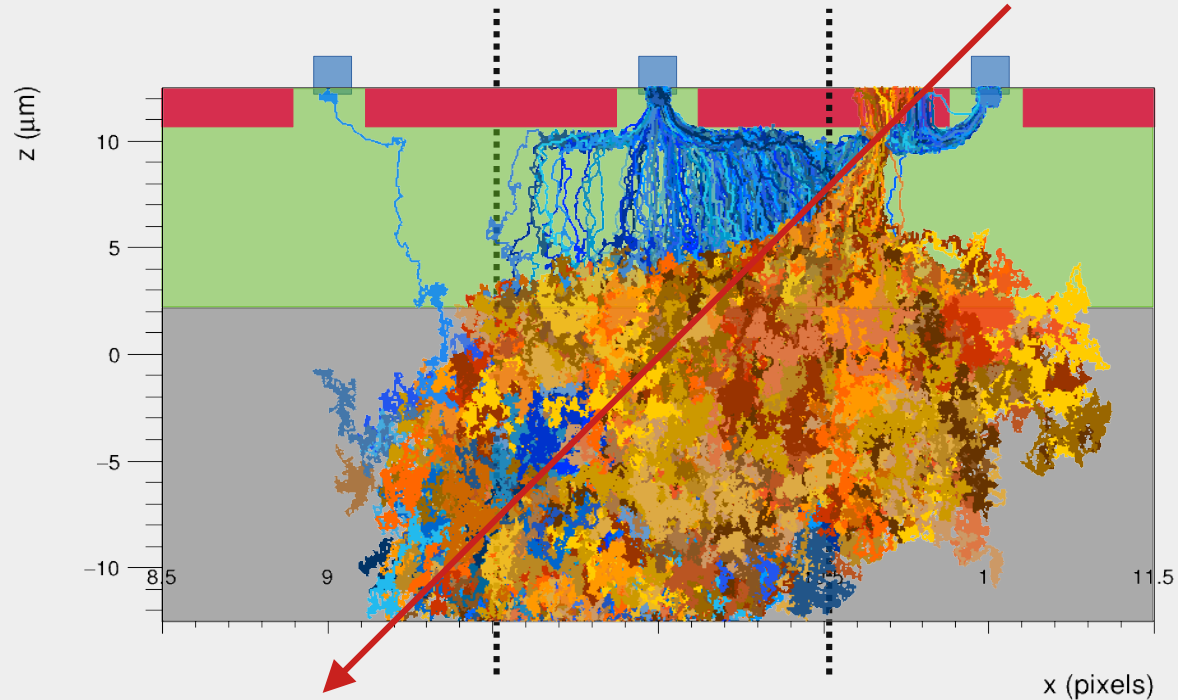
# Some Application Highlights

MAPS, PET Scanners, 3D Sensors, Impact Ionization, ...



# Simulating a MAPS Sensor

- MIP entering sensor at 45deg
- Applying TCAD electric field
  - Bias voltage -1.2 V
  - Depletion depth 10  $\mu\text{m}$
  - Setting doping for epi & subs.
- Carrier mobility:
  - Masetti-Canali model (doping dependent)
  - Integrating for 50 ns
- Recombination: combined SRH-Auger model



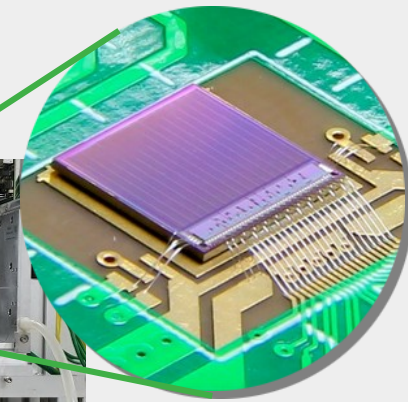
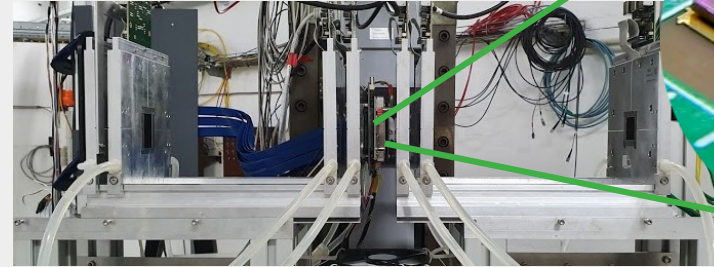
■ electrons  
■ holes

- Diffusion dominant in undepleted volume
- Carrier drift obeys sensor features (p-wells), collection at electrodes

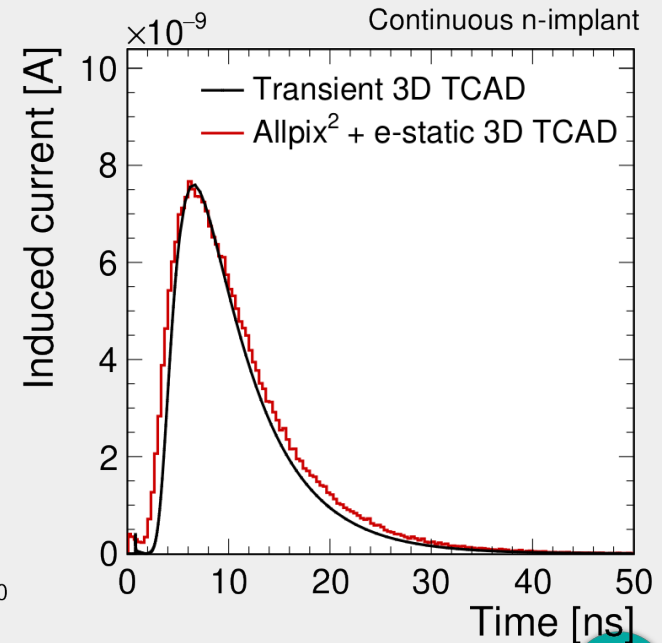
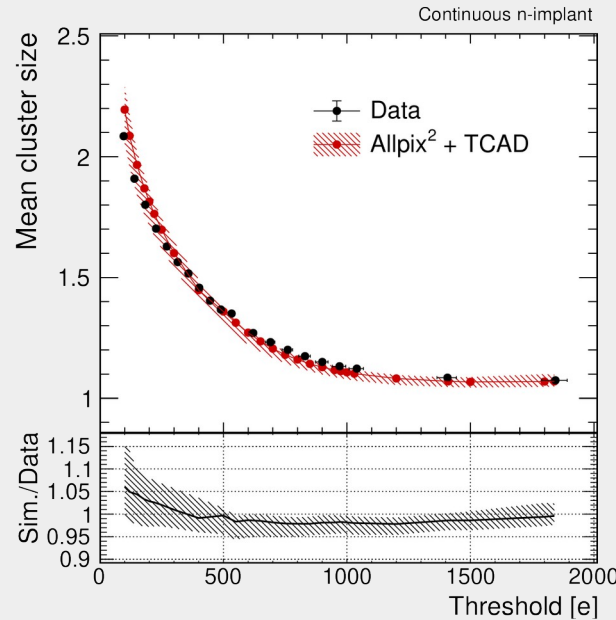
# Comparison with Testbeam Data

NIMA 1031 (2022) 166491  
doi:10.1016/j.nima.2022.166491

- CLICTD prototype for CLICdet tracking detector
- Validation of MC simulation with data recorded at DESY II Testbeam



- Excellent match of position resolution as function of threshold
- Comparison of TCAD transient simulation with Shockley-Ramo MC simulation
  - Very good match, also across different sensor designs
- More MAPS simulation examples:  
[Talk by Håkan Wennlöf](#)

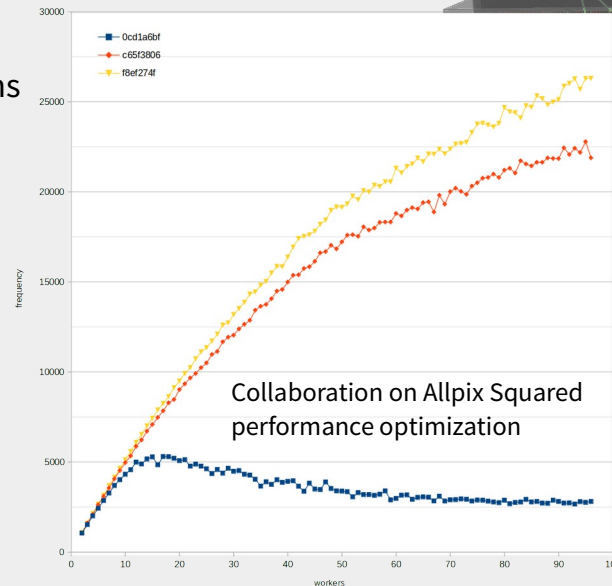


# The 100 $\mu$ PET Project

New generation of PET scanners for high-res. molecular imaging

Talk by Mateus Vicente yesterday

- 4 Sectors, each 60 detection layers, monolithic Si sensors
- Simulating full setup with Allpix Squared
  - Script to generate geometry setup
  - Placement of sensors, support, absorbers
  - Interaction from Geant4 module: Positron anni. and MFP, Photon Interactions
  - Charge carrier propagation
  - Electronics response (pixel threshold 10 keV)
  - Clustering
- Custom particle sources: images to simulate realistic phantoms
- High-rate event generation for "realistic data-sets" with  $\sim 10^{10}$  events



3mm Al  
Inner Cooling  
Block

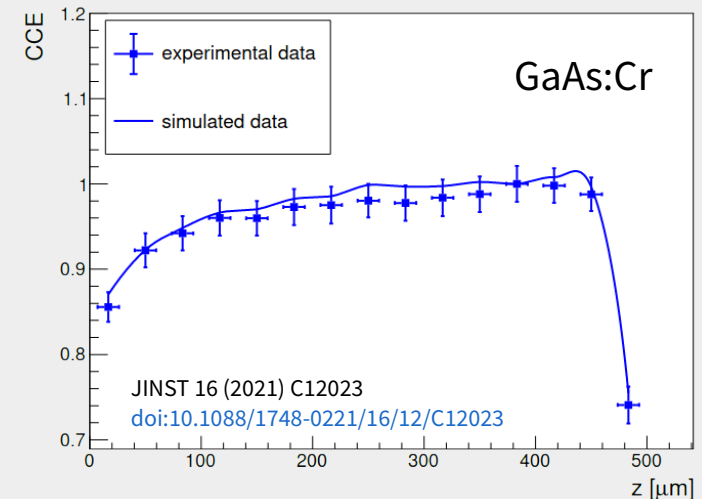
# Non-Silicon Semiconductor Sensors

Allpix<sup>2</sup> supports a range of semiconductor materials:

- Selection of sensor material in det. model
- Definition of sensor materials impacts ...
  - Material in Geant4 geometry
  - Charge carrier creation energy
  - Fano factor
  - Mobility model, recombination, ...

Material	Charge Creation Energy [eV]	Fano factor	Sources
Silicon	3.64	0.115	[25], [26]
Germanium	2.97	0.112	[27]
Gallium Arsenide	4.2	0.14	[28]
Cadmium Telluride	4.43	0.24	[29], [30]
Cadmium Zinc Telluride Cd <sub>0,8</sub> Zn <sub>0,2</sub> Te	4.6	0.14	[31], [32]
Diamond	13.1	0.382	[33], [33]
Silicon Carbide (4H-SiC)	7.6	0.1	[34], [35]

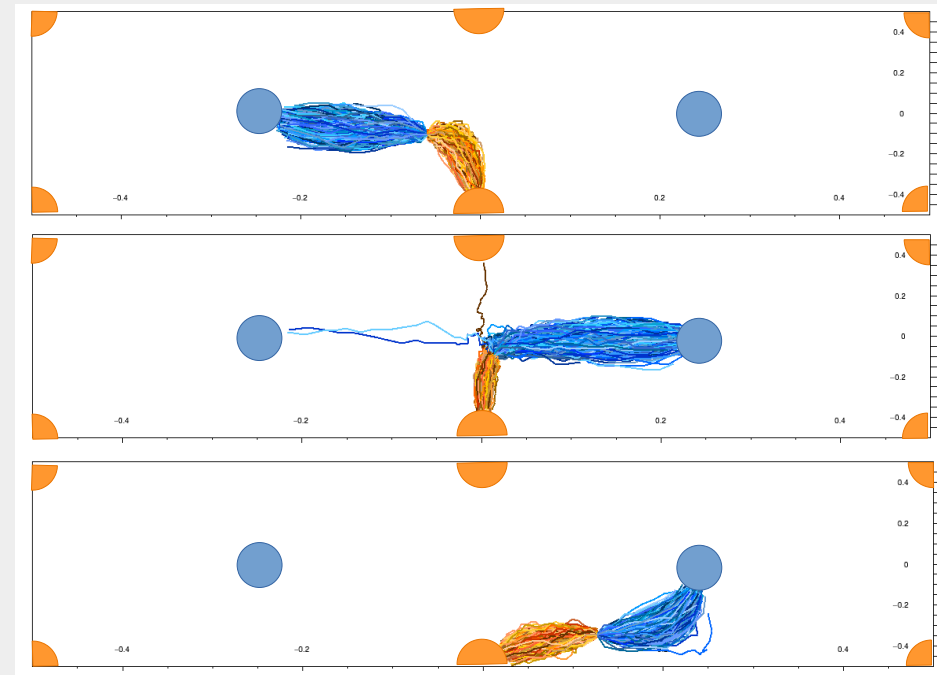
Example: Benchmark simulation using GaAs:Cr sensors,



# Simulation of 3D Sensors

- Definition of per-pixel implants via detector model
  - Position with respect to pixel center
  - Shape & orientation
  - front/backside
- Add as many implants as required, syntax similar to support layers (PCB etc)
- Collision detection of charge carriers with implants; motion stops immediately at implant border
- First simulations with ATLAS 3D sensor geometry
  - Two central front-side columns (collect charge)
  - Six Ohmic backside contact columns

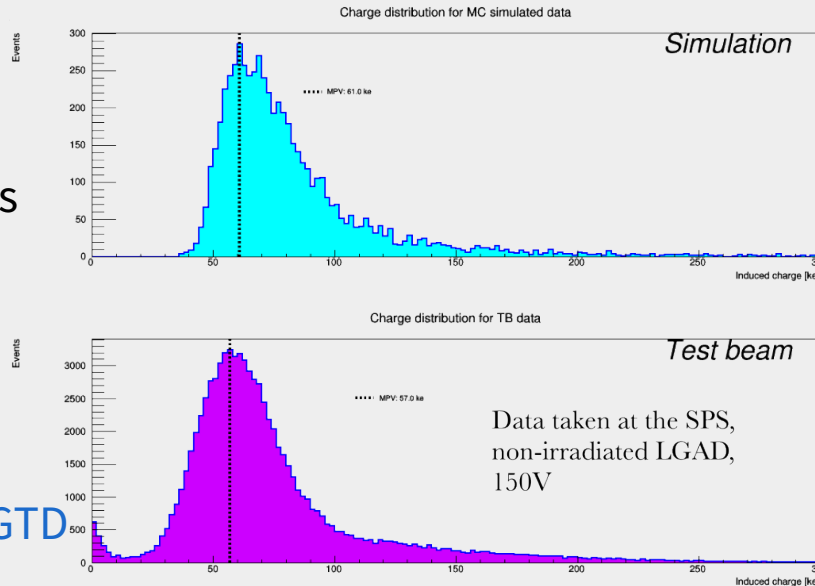
single pixel,  
top projection of 3D drift



# Impact Ionization

charge multiplication through impact ionization available

- Multiple models available, selection via configuration file:
  - Massey
  - van Overstraeten-de Man
  - Okuto-Crowell
  - Bologna
  - Optimized parameters for LGADs (RD50 work)
- Validation of algorithm, comparison of models e.g. in context of ATLAS HGTD



coefficient  $\alpha$  and the length of the step  $l$  performed in the respective electric field. If the electric field strength stays below a configurable threshold  $E_{thr}$ , unity gain is assumed:

$$g(E, T) = \begin{cases} e^{l\alpha(E, T)} & E > E_{thr} \\ 1.0 & E < E_{thr} \end{cases} \quad (6.12)$$

The following impact ionization models are available:

### 6.3.1 Massey Model

The Massey model [35] describes impact ionization as a function of the electric field  $E$ . The ionization coefficients are parametrized as

$$\alpha(E, T) = Ae^{-\frac{B(T)}{E}}, \quad (6.13)$$

where  $A$  and  $B(T)$  are phenomenological parameters, defined for electrons and holes respectively. While  $A$  is assumed to be temperature-independent, parameter  $B$  exhibits a temperature dependence and is defined as

$$B(T) = C + D \cdot T. \quad (6.14)$$

The parameter values implemented in Allpix<sup>2</sup> are taken from Section 3 of [35] as:

$$\begin{aligned} A_e &= 4.43 \times 10^5 / \text{cm} & A_h &= 1.13 \times 10^6 / \text{cm} \\ C_e &= 9.66 \times 10^5 \text{ V/cm} & C_h &= 1.71 \times 10^6 \text{ V/cm} \\ D_e &= 4.99 \times 10^2 \text{ V/cm/K} & D_h &= 1.09 \times 10^3 \text{ V/cm/K} \end{aligned}$$

for electrons and holes, respectively.

The model is selected in the configuration file via the parameter `multiplication_model`.

### van Overstraeten-De Man Model

The van Overstraeten-De Man model [36] describes impact ionization using Chynoweth's law,

$$\alpha(E, T) = \gamma(T) \cdot a_\infty \cdot e^{-\frac{\gamma(T) \cdot b}{E}}, \quad (6.15)$$

where two sets of impact ionization parameters  $p = \{a_\infty, b\}$  are used depending on the

$$p = \begin{cases} p_{low} & E < E_0 \\ p_{high} & E > E_0 \end{cases} \quad (6.16)$$

selection of the ionization coefficient is performed via the  $\gamma(T)$  parameter following the ATLAS user manual as:

$$\gamma(T) = \left( \frac{0.063 \times 10^6 \text{ eV}}{28.6173 \times 10^{-5} \text{ eV/K} \cdot T_0} \right) \cdot \tanh \left( \frac{0.063 \times 10^6 \text{ eV}}{28.6173 \times 10^{-5} \text{ eV/K} \cdot T} \right)^{-1} \quad (6.17)$$





# Contribute to the Development of Allpix Squared

```
Module {
    ~Module() = delete;
}

class ModuleManager;
class Messenger;

// Base constructor for unique modules
// @param config Configuration for this module
Module(ModuleManager &mm, Configuration& config);

// Base constructor for detector modules
// @param config Configuration for this module
// @param detector Detector bound to this module
// @note Detector modules should not forget to forward their detector to the base class
// @ref InvalidModuleStateException will be raised if the module failed to load
Module(ModuleManager &mm, Configuration& config, std::shared_ptr<Detector> detector);

// Essential virtual destructor.
// @note This destructor ensures all delegates linked to this module
// are properly cleaned up.
virtual ~Module();

// A module is not allowed
// to be copied or moved.
Module(const Module&) = delete;
Module(Module&) = delete;

// This module does not have behaviour (not possible with references)
Module(const Module&) noexcept = delete;
Module(Module&) noexcept = delete;
```



# How To Contribute – A Cookbook

- **Get in touch** – mail, forum, issue tracker, ...  
Let's discuss the idea, maybe we have input, maybe others are working on it already

- **Fork the repository**

Creating your own copy of the code with which you can mess as much as you want

- **Start hacking**

Implement the desired functionality, come back to us when you have doubts or questions

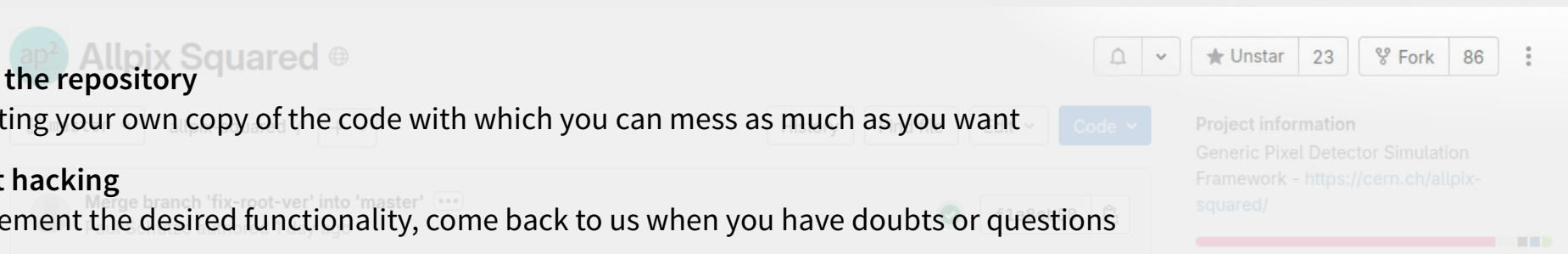
- **Make sure the CI passes**

Enable the CI in your fork and publish your new code there – check that the CI works!

- **File a Merge Request**

This provides us a central point to discuss and review all your code changes

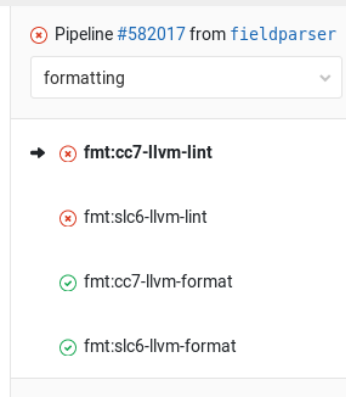
- **See your code being merged and published!**



```

3 warnings treated as errors
/builds/allpix-squared/allpix-squared/src/core/geometry/Detector.cpp:185:29: error:
parameter 'field' is passed by value and only copied once; consider moving it to avoid
unnecessary copies [performance-unnecessary-value-param,-warnings-as-errors]
    electric_field_.setGrid(field, sizes, scales, offset, thickness_domain);
                           ^
                           std::move( )
/builds/allpix-squared/allpix-squared/src/core/geometry/Detector.cpp:191:33: error:
parameter 'function' is passed by value and only copied once; consider moving it to avoid
unnecessary copies [performance-unnecessary-value-param,-warnings-as-errors]
    electric_field_.setFunction(function, thickness_domain, type);
                              ^
                              std::move( )
/builds/allpix-squared/allpix-squared/src/core/geometry/DetectorField.hpp:51:27: error:
member initializer for 'field_type_' is redundant [modernize-use-default-member-init,-
warnings-as-errors]
    DetectorField() : field_type_(FieldType::NONE){};
                    ^

```



# Summary



ap<sup>2</sup>  
allpix squared

# Summary

- Semiconductor Detector Monte Carlo simulations:  
vital component of understanding & interpreting detector performance
- Allpix Squared:  
comprehensive MC simulation framework for semiconductor detectors
  - integrates existing toolkits
  - provides validated algorithms
  - is easy-to-get-started and well documented
- Used in many areas within & outside of particle physics
- Continuous development and support, many new features already underway



Use, simulate, contribute, share!

This project has received funding from the European Union's Horizon 2020 Research and Innovation programme under Grant Agreement No 101004761.



# Allpix Squared Resources



Website

<https://cern.ch/allpix-squared>



Repository

<https://gitlab.cern.ch/allpix-squared/allpix-squared>



Docker Images

[https://gitlab.cern.ch/allpix-squared/allpix-squared/container\\_registry](https://gitlab.cern.ch/allpix-squared/allpix-squared/container_registry)



User Forum:

<https://cern.ch/allpix-squared-forum/>



Mailing Lists:

allpix-squared-users <https://e-groups.cern.ch/e-groups/Egroup.do?egroupId=10262858>

allpix-squared-developers <https://e-groups.cern.ch/e-groups/Egroup.do?egroupId=10273730>



User Manual:

<https://cern.ch/allpix-squared/usermanual/allpix-manual.pdf>

